

1. Solar cell**[10 M]**

- a) Write the equations for $I - V$ characteristics and $P - V$ characteristics of pn junction solar cell. [BT 1][2 M]
- b) Derive the equation to determine the operating voltage for maximum power generation V_m in terms of the photocurrent I_L and reverse saturation current I_S . [BT 3][4 M]
- c) The reverse saturation current density for a solar cell pn junction is $3.6 \cdot 10^{-11} A/cm^2$. What is the photocurrent density required to generate open circuit voltage of 0.60 V. [BT 4][4 M]

PART - B

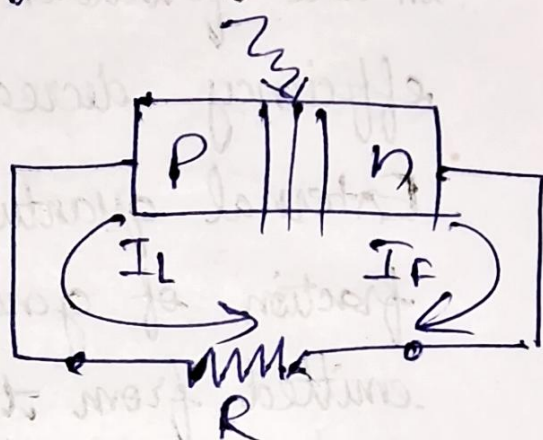
① Solar cell

a) Write the equations for I-V & P-V characteristics of pn junction solar cell.

Solution:

$$I = I_L - I_F$$

$$I = I_L - I_s \left[\exp\left(\frac{eV}{k_B T}\right) - 1 \right]$$



and $P = VI$

$$V = IR$$

$$P = V \left[I_L - I_s \left\{ \exp\left(\frac{eV}{k_B T}\right) - 1 \right\} \right]$$

So we have $P(V)$. and we have conditions for optimization.

b) Derive the equation for determining the operating voltage for maximum power generation V_m in terms of I_L and I_s .

$$\frac{dP}{dV} = 0 \Leftrightarrow I_L - I_s \left\{ \exp\left(\frac{eV}{k_B T}\right) - 1 \right\} + V \left[-I_s \frac{e}{k_B T} \exp\left(\frac{eV}{k_B T}\right) \right] = 0$$

$$\Leftrightarrow I_L - I_s \left\{ \exp\left(\frac{V}{V_t}\right) - 1 \right\} - I_s \frac{V}{V_t} \exp\left(\frac{V}{V_t}\right) = 0$$

$$\Leftrightarrow \exp\left(\frac{V}{V_t}\right) \left\{ I_s + I_s \frac{V}{V_t} \right\} = I_L + I_s$$

$$\Leftrightarrow \exp\left(\frac{V}{V_t}\right) \left(1 + \frac{V}{V_t} \right) = 1 + \frac{I_L}{I_s}$$

c) The reverse saturation current density for a solar cell pn junction is $3.6 \cdot 10^{-11} \text{ A/cm}^2$. What is the photocurrent density required to generate open circuit voltage of 0.60 V ?

Solution:

At open circuit conditions

$$I = 0 \Rightarrow I_L = I_s \left[\exp\left(\frac{V_{oc}}{V_t}\right) - 1 \right]$$

$$\Rightarrow \exp\left(\frac{V_{oc}}{V_t}\right) = 1 + \frac{I_L}{I_s}$$

$$\Rightarrow \frac{V_{oc}}{V_t} = \ln\left(1 + \frac{I_L}{I_s}\right)$$

$$\Rightarrow V_{oc} = V_t \ln\left(1 + \frac{I_L}{I_s}\right)$$

$$0.60 = 0.0259 \ln\left(1 + \frac{I_L}{I_s}\right)$$

$$\Rightarrow \ln\left(1 + \frac{I_L}{I_s}\right) = \frac{0.60}{0.0259}$$

$$\ln\left(1 + \frac{I_L}{I_s}\right) = 23.16$$

$$\Rightarrow 1 + \frac{I_L}{I_s} = \exp(23.16)$$

$$1 + \frac{I_L}{I_s} = 1.14 \cdot 10^{10}$$

$$I_L \approx I_s \cdot 1.14 \cdot 10^{10}$$

$$= 3.6 \cdot 10^{-11} \cdot 1.14 \cdot 10^{10}$$

$$= 4.1 \cdot 10^{-1} \text{ A/cm}^2$$

$$= 0.41 \text{ A/cm}^2$$

2. n_0p_0 product in extrinsic semiconductor**[10 M]**

- a) Design a new semiconductor material. It has to be p type and doped with $N_a = 5 \cdot 10^{15} \text{ cm}^{-3}$ acceptor atoms. Assume complete ionization and assume $N_d = 0$. The effective density of states functions are $N_c = 1.2 \cdot 10^{19} \text{ cm}^{-3}$ and $N_v = 1.8 \cdot 10^{19} \text{ cm}^{-3}$ at $T = 300\text{K}$. The requirement is that the hole concentration must not exceed $5.08 \cdot 10^{15} \text{ cm}^{-3}$ at $T = 350\text{K}$. What is the minimum bandgap energy required in this material? You can assume the n_0p_0 product rule is valid for extrinsic semiconductor also. [Hint: Apply the n_0p_0 product rule on the charge neutrality condition $n_0 + N_a^- = p_0 + N_d^+$.]

[BT 6][10 M]

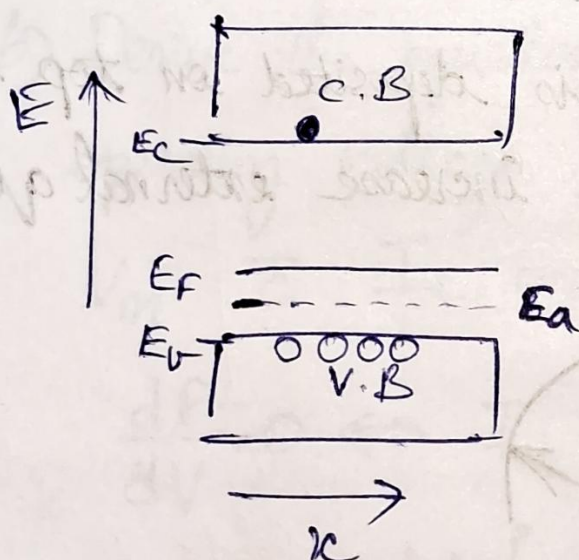
② No P_0 product

a) Design a new semiconductor. It has to be p-type and doped with $N_a = 5 \cdot 10^{15} \text{ cm}^{-3}$ acceptor atoms. Assume complete ionization and assume $N_d = 0$. The effective density of states functions are $N_c = 1.2 \cdot 10^{19} \text{ cm}^{-3}$ and $N_v = 1.8 \cdot 10^{19} \text{ cm}^{-3}$ at $T = 300 \text{ K}$.

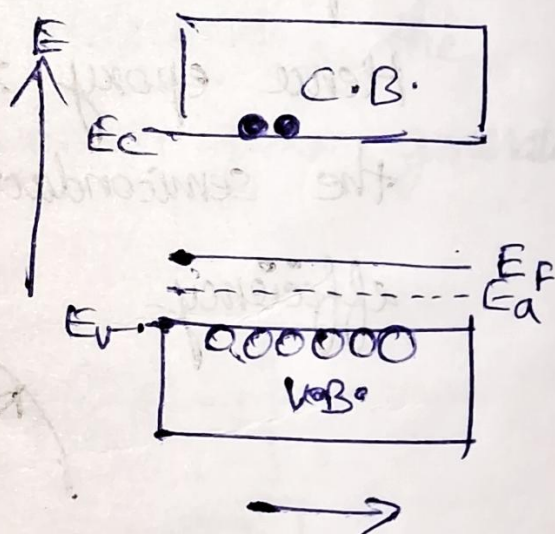
The requirement is that the hole concentration must not exceed $5.08 \cdot 10^{15} \text{ cm}^{-3}$ at $T = 350 \text{ K}$. What is the minimum bandgap energy required in this material?

Solution:

@ $T = 300 \text{ K}$



@ $T = 350 \text{ K}$



As temperature increases, thermally generated electron-hole pairs increase in addition to the majority ^{holes} carriers due to acceptors.

@ $T=300$ let n_0

@ $T=350K$,

let n_0 - electron (minority)

& p_0 - hole (majority) be in p-type

Now acceptors contribute holes.

After ionization, they are ionized to Na^-

In p type,

charge neutrality enforces

total negative charge = total positive charge

$$n_0 + Na^- = p_0$$

Now $n_0 p_0$ product rule relates

n_0 to p_0

$$\Rightarrow n_0 p_0 = n_i^2$$

$$\Rightarrow n_0 = \frac{n_i^2}{p_0}$$

n_i is the intrinsic conc

@ $T=350$

$$\therefore \frac{n_i^2}{p_0} + Na^- = p_0$$

Due to complete ionization, $Na^- = Na$

so that intrinsic conc is given by $= 5 \cdot 10^{15} \text{ cm}^{-3}$

$$\frac{n_i^2}{p_0} = p_0 - Na$$

$$\text{Now } p_0 = 5.08 \cdot 10^{15}$$

$$\text{so that } n_i^2 = (5.08 - 5) \cdot 10^{15} \cdot 5.08 \cdot 10^{15}$$

$$\Rightarrow n_i^2 = 0.4064 \cdot 10^{30}$$

⚡ Intrinsic concentration varies with temperature as

$$n_i^2 = N_c N_v \exp\left(-\frac{E_g}{k_B T}\right)$$

∴ N_c & N_v vary as $T^{3/2}$ individually

$$\therefore n_i^2 \propto T^3 \exp\left(-\frac{E_g}{k_B T}\right)$$

$$\therefore \frac{n_i^2(@350K)}{T_{350}^3 \exp\left(-\frac{E_g}{k_B T_{350}}\right)} = \frac{n_i^2(@300K)}{T_{300}^3 \exp\left(-\frac{E_g}{k_B T_{300}}\right)}$$

$$= \frac{N_c N_v \exp\left(-\frac{E_g}{k_B T_{300}}\right)}{T_{300}^3 \exp\left(-\frac{E_g}{k_B T_{300}}\right)}$$

$$\Rightarrow \exp\left(-\frac{E_g}{k_B T_{350}}\right) = \left(\frac{T_{300}}{T_{350}}\right)^3 \frac{n_i^2(@350K)}{N_c N_v}$$

$$\Rightarrow \exp\left(-\frac{E_g}{k_B T_{350}}\right) = \left(\frac{300}{350}\right)^3 \frac{0.4064 \cdot 10^{30}}{1.2 \cdot 10^{19} \cdot 1.8 \cdot 10^{19}}$$

$$\Rightarrow \exp\left(-\frac{E_g}{k_B T_{350}}\right) = 0.118 \cdot 10^{-8}$$

$$\Rightarrow \frac{E_g}{k_B T_{350}} = 20.55$$

$$\therefore E_g = 0.62 \text{ eV}$$

$$\Rightarrow E_g = k_B T_{350} \cdot 20.55 = 0.0259 \left(\frac{350}{300}\right) \cdot 20.55$$

3. Blackbody radiation and optical absorption

[10 M]

- a) The Planck's blackbody radiation law is given by

$$I(\nu) = \frac{2h\nu^3}{c^2} \frac{1}{\exp\left(\frac{h\nu}{k_B T}\right) - 1}$$

where $I(\nu)$ is the irradiance at a given frequency ν and temperature T . Find the expression for wavelength λ_m corresponding to maximum irradiance in terms of temperature T . [BT 3][4 M]

- b) An alien ship crash landed onto Earth's surface. From the debris, the solar panel used for power generation is found to have a band gap of 5 eV. Estimate the temperature of the alien Sun. [BT 5][4 M]
- c) Is the solar panel useful for applications on Earth? Why or why not? [BT 2][2 M]

(3) Black body radiation and optical absorption

a) Planck's blackbody radiation law is

$$I(\nu) = \frac{2h\nu^3}{c^2} \frac{1}{\exp\left(\frac{h\nu}{k_B T}\right) - 1}$$

where I is the irradiance at a given frequency ν and temperature T .

Find the expression for wavelength λ_m corresponding to maximum irradiance $\propto T$.

Solution

For Wien's displacement law derivation
 ☆ it is useful to work with irradiance
 as a function of wavelength

$$I(\nu) d\nu = -I(\lambda) d\lambda$$

Now $\frac{d\nu}{d\lambda}$ sign indicates changes in ν and λ are opposite to each other

$$I(\lambda) = -I(\nu) \frac{d\nu}{d\lambda}$$

$$\text{But } \nu = \frac{c}{\lambda}$$

$$\Rightarrow \frac{d\nu}{d\lambda} = c \frac{d(\frac{1}{\lambda})}{d\lambda} = -\frac{c}{\lambda^2}$$

$$\therefore I(\lambda) = \frac{c}{\lambda^2} I(\nu)$$

$$= \frac{2hc}{c^2} \frac{c^3}{\lambda^3 \lambda^2} \frac{1}{\exp\left(\frac{hc}{\lambda k_B T}\right) - 1}$$

$$I(\lambda) = \frac{2hc^2}{\lambda^5} \frac{1}{\exp\left(\frac{hc}{\lambda k_B T}\right) - 1}$$

Now λ_{max} is given by

$$\left. \frac{dI}{d\lambda} \right|_{\lambda_{\text{max}}} = 0 \Leftrightarrow \frac{-5}{\lambda^6} \frac{1}{\exp\left(\frac{hc}{\lambda k_B T}\right) - 1} +$$

$$\frac{1}{\lambda^5} \frac{1}{\left[\exp\left(\frac{hc}{\lambda k_B T}\right) - 1\right]^2} \frac{hc}{k_B T} \exp\left(\frac{hc}{\lambda k_B T}\right) \frac{1}{\lambda^2} = 0$$

$$\Leftrightarrow -5 \left[\exp\left(\frac{hc}{\lambda k_B T}\right) - 1 \right] + \frac{hc}{\lambda k_B T} \exp\left(\frac{hc}{\lambda k_B T}\right) = 0$$

$$T \quad x = \frac{hc}{\lambda_{\max} k_B T}$$

then

$$-5(e^x - 1) + xe^x = 0$$

$$5(1 - e^x) + xe^x = 0$$

$$5(e^{-x} - 1) + x = 0$$

$$x = 5(1 - e^{-x})$$

In the short wavelength limit

$$x \gg e^{-x}$$

$$\Rightarrow x \approx 5$$

$$\Rightarrow \frac{hc}{\lambda_{\max} k_B T} = 5$$

$$\Rightarrow \lambda_{\max} T = \frac{hc}{5 k_B}$$

$$= \frac{6.625 \cdot 10^{-34} \cdot 3 \cdot 10^8}{5 \cdot 1.38 \cdot 10^{-23}}$$

$$\boxed{\lambda_{\max} T = 2.88 \cdot 10^{-3} \text{ m K}}$$

(b) Alien ship has crash landed onto Earth's surface. From the debris, solar panel used for power generation is found to have a band gap of 5 eV. Estimate the temperature of alien Sun.

Solution:

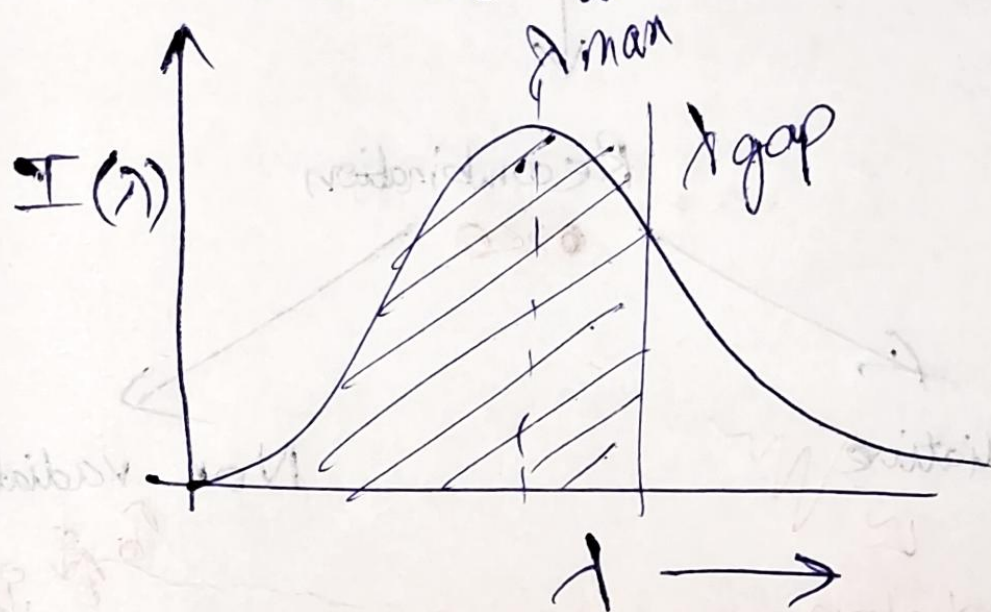
λ_{gap} of solar panel material is

$$(\mu\text{m}) \lambda_{\text{gap}} = \frac{1.24}{E_{\text{gap}} (\text{eV})}$$

$$= \frac{1.24}{5}$$

$$\lambda_{\text{gap}} = 0.248 \mu\text{m}$$

Now if the alien Sun can be assumed to be a black body, its radiation spectrum should look like alien.



Now if the aliens are logical beings they should be using solar panel whose λ_{gap} covers most of the spectrum radiation. So λ_{gap} If $\lambda_{\text{max}}^{\text{alien}}$ is the maximum ^{irradiance} wavelength, then $\lambda_{\text{max}}^{\text{alien}} \leq \lambda_{\text{gap}}$

$$\Rightarrow \lambda_{\text{max}}^{\text{alien}} \leq 0.248 \mu\text{m}$$

Now the $\lambda_{\text{max}}^{\text{alien}}$ is related to Wiens displacement law by:

$$\lambda_{\text{max}}^{\text{alien}} T_{\text{alien}} = 2.88 \cdot 10^{-3} \text{ mK}$$

$$\Rightarrow T_{\text{alien}} = \frac{2.88 \cdot 10^{-3} \text{ mK}}{\lambda_{\text{max}}^{\text{alien}}}$$

$$\Rightarrow T_{\text{alien}} \geq \frac{2.88 \cdot 10^{-3}}{0.248 \cdot 10^{-6}}$$

$$= 11.6 \cdot 10^3 \text{ K}$$

$$T_{\text{alien}} = 11,600 \text{ K}$$

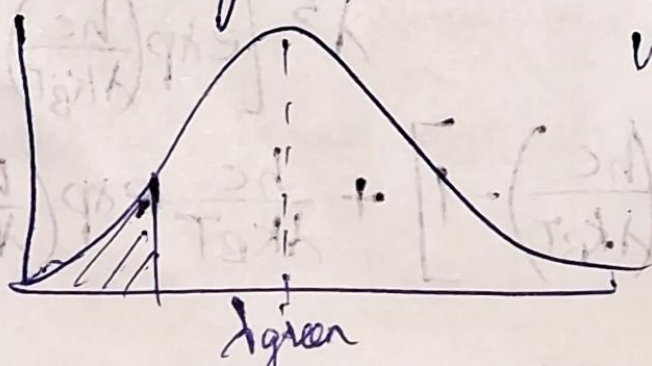
(C) Is the solar panel useful for applications on Earth? why or why not?

Solution:

At Earth, the solar radiation peaks at green colour

$$\lambda_{\text{green}} = 0.51 \mu\text{m}$$

whereas ~~$\lambda_{\text{max}}^{\text{alien}}$~~



$$\lambda_{\text{gap}} = 0.248 \mu\text{m}$$

So very small portion of spectrum
can be absorbed by the solar panel.

Thus, it would not be a very efficient
solar cell.

END OF PART-B